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Temperature Dependent Magnetic Anisotropy in (Ga,Ma)As Layers

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It is demonstrated by SQUID magnetization measurements that (Ga,Mn)As films can exhibit rich characteristics of magnetic anisotropy depending not only to the epitaxial strain but being strongly influenced by the hole and Mn concentration, and temperature. This behavior reflects the spin anisotropy of the valence subbands and corroborates predictions of the mean field Zener model of the carrier mediated ferromagnetism in III-V diluted magnetic semiconductors with Mn. At the same time the existence of in-plane uniaxial anisotropy with [110] the easy axis is evidenced. This is related to the top/bottom symmetry breaking, resulting in the lowering of point symmetry of (Ga,Mn)As to the C_{2v} symmetry group. The latter mechanism coexists with the hole-induced cubic anisotropy, but takes over close to T_C.

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The discovery of carrier-mediated ferromagnetism at temperatures in excess of 100 K in (III,Mn)V dilute magnetic semiconductors (DMS) grown by molecular beam epitaxy (MBE) has made it possible to combine complementary properties of semiconductor quantum structures and ferromagnetic systems in single devices, paving the way for the development of functional semiconductor spintronics.[1] Therefore, the understanding of magnetic anisotropy in these systems and the demonstration of methods for its control is timely and important. It has been known, since the pioneering works of Munekata *et al.*[2] and Ohno *et al.*,[3] that ferromagnetic (In,Mn)As and (Ga,Mn)As films are characterized by a substantial magnetic anisotropy. Remarkably, due to magnetic dilution, the ordinary shape anisotropy plays here only a marginal role and, accordingly, explains neither direction nor large magnitude of the observed anisotropy field H_{un}.

It has been found by anomalous Hall effect studies,[3] that the direction of the easy axis is mainly controlled by epitaxial strain in these systems. Generally, for layers under tensile biaxial strain [like (Ga,Mn)As on a (In,Ga)As buffer] perpendicular-to-plane magnetic easy axis has been observed (perpendicular magnetic anisotropy, PMA). In contrast, layers under compressive biaxial strain [as canonical (Ga,Mn)As on a GaAs substrate] have been found to develop in-plane magnetic easy axis (in-plane magnetic anisotropy, IMA). At first glance, this sensitivity to strain appears surprising, as the Mn ions are in the orbital singlet state $^6A_1$. For such a state, the strain-induced single ion anisotropy is expected to be rather small and, indeed, electron paramagnetic resonance (EPR) studies of Mn in GaAs yielded relevant spin Hamiltonian parameters by two orders of magnitude too small to explain the observed values of H_{un}.[4]

In the system in question, however, the ferromagnetic spin-spin exchange interaction is mediated by the band holes, whose Kohn-Luttinger amplitudes are primarily built up of anion p orbitals in tetrahedrally coordinated semiconductors. Furthermore, in semiconductors, in contrast to metals, the Fermi energy is usually smaller than the atomic spin-orbit energy. Hence, as noted by some of the present authors and co-workers,[5,6] the strain or confinement-induced anisotropy of the valence band can result in a sizable anisotropy of spin properties. Indeed, the quantitative calculation within the mean-field Zener model,[6,7] in which the valence band is represented by the 6×6 Luttinger hamiltonian, explains the experimental values of H_{un} in (Ga,Mn)As with the accuracy better than a factor of two. Moreover, by combining theories of magnetic anisotropy[6,7,8] and of magnetic stiffness,[9] it has been possible to describe the width of stripe domains in (Ga,Mn)As PMA films.[10] However, the theories in question[7,8] contain a number of predictions that call for a detail experimental verification.

In this communication we present magnetic anisotropy studies carried out by direct magnetization measurements in a dedicated SQUID magnetometer. Our results demonstrate that the temperature-induced reorientation of the easy axis from [001] to [100], and then to [110] or equivalent directions occurs in films of (001) (Ga,Mn)As on GaAs with appropriately low values of p. We argue that these findings corroborate the above mentioned theoretical expectations. However, the data collected near T_C reveal a non-equivalence of the [110] and $[\bar{1}10]$ crystal directions, the latter corresponding to the hard axis. This points to the existence of a mechanism lowering the point symmetry from D_{2d} to C_{2v}. We find that this particular anisotropy develops independently of p. Such a symmetry breaking has already been inferred from transport data[11,12] and Kerr rotation.[13] Finally, we find that in another class of samples the hard axis remains oriented along the $[\bar{1}10]$ direction but the three other main directions ([100], [110] and [010]) become equally easy. We discuss reasons and consequences of these unusual

FIG. 1: Magnetic field (a,b) and temperature (c) dependent magnetization measured for parallel (full points) and perpendicular (open points) orientations with respect to the magnetizing field. Note the flip of the easy axis at T_{L}.

$H_{\mathrm{FC}} \parallel [001]$, comparing to the case of parallel arrangement, $H_{\mathrm{FC}} \parallel [100]$. This reconfirms the appearance of PMA for large values of spontaneous magnetization M_s in this film despite the presence of a sizable compressive strain. The PMA holds until a certain temperature T_{L} ($T_{\mathrm{L}} \simeq 16$ K in this case), at which a sudden drop of the signal is detected in the perpendicular orientation. Nevertheless, the M_{REM} signal for the parallel case remains small. This seems to contradict our scenario, according to which the easy axis is in-plane for $T > T_{\mathrm{L}}$. We note, however, that the spontaneous flip of magnetization to the in-plane configuration results in a *demagnetized* state. Actually, a visible maximum of the parallel M_{REM} between T_{L} and T_{C} reflects the presence of the field H_r, which magnetizes the film once the in-plane anisotropy and coersive fields become sufficiently small. Indeed, a temperature cycling of about $\Delta T = 2$ K just below this maximum increases the magnitude of the in-plane magnetization by a factor of three, as shown in Fig. 2.

We have found the temperature-induced cross over from PMA to IMA described above in five other samples of (Ga,Mn)As.[15] Recently, this effect has been detected in (Al,Ga,Mn)As under similar conditions.[16] According

FIG. 3: Experimental evidence for the easy axis switching from [100] to [110] direction (at $\sim$ 10 K) and for the uniaxial anisotropy along [110] direction in $\mathrm{Ga_{0.968}Mn_{0.032}As}$. The magnetic remanence was measured for four major in-plane directions and its magnitude is normalized by the data for the [110] case.

in Fig. 3, by presenting M_{REM} measured along the four principal in-plane crystallographic directions [100], [110], [010], and [$\bar{1}$10], exemplify this case. We note that at low temperatures the highest values of M_{REM} are collected along $\langle 100\rangle$ directions. However, this alters at about 10 K, above which the [110] becomes the most preferred direction in the system. It is not only that M_{REM} is the stronger for this direction but also this remanence is by a factor of $\sqrt{2}$ larger than that for the $\langle 100\rangle$ directions, as is expected from simple geometric considerations.

Surprisingly, however, the data reveals the existence of an uniaxial anisotropy along [110]. As shown in Fig. 3, M_{REM} measured along [$\bar{1}$10] direction vanishes completely above 15 K indicating that this is the hard direction of the system. At the same time, the magnitude of M_{REM} is the same for both $\langle 100\rangle$ directions. We argue that this is the result of the lack of the inversion symmetry in (Ga,Mn)As (001) films. Due to the biaxial strain, the initial T_d point symmetry of zinc-blende structure is lowered to D_{2d}. But the bottom (Ga,Mn)As/GaAs interface is different than the top (Ga,Mn)As/vacuum one. This further lowers the symmetry to C_{2v}, where the three principal directions are: [001], [110] and [$\bar{1}$10]. They are not equivalent, in C_{2v} the [110] $\Leftrightarrow$ [$\bar{1}$10] symmetry gets broken, while the [100] $\Leftrightarrow$ [010] one is maintained through reflectivity operations by the (110) and ($\bar{1}$10) planes, which conforms with the presented results. Since the cubic-like anisotropy energy is proportional to M_s^4 whereas the uniaxial one to M_s^2, the latter is dominating at high temperatures, where M_s is small. We also note that when $M_{\mathrm{REM}}^{[\bar{1}10]}$ vanishes the $M_{\mathrm{REM}}^{\langle 100\rangle}/M_{\mathrm{REM}}^{[110]}$ ratio drops to $\sqrt{2}/2$, the value expected for the easy axis along [110].

Another class of samples are those, in which relatively high values of p and/or x make the cubic easy axis to be oriented along $\langle 100\rangle$ in the whole relevant temperature range. In such samples, the coexistence of the cubic and uniaxial anisotropy leads to the case ”not [$\bar{1}$10]”, as presented in Fig. 4(a). This is generally the [100] easy axis

FIG. 4: Magnetization dependencies evidencing "not [$\bar{1}10$]" anisotropy developing in Ga$_{0.935}$Mn$_{0.065}$As at temperature close to T_{C}.

samples in which the [110] direction gets equally easy as the [100] directions at high temperatures. So, close to T_{C} these three major directions are virtually equivalent, while the [$\bar{1}10$] axis stays hard. As shown in Fig. 4(b), such an anisotropy changes considerably the shape of the hysteresis loop, yielding $M^{[\bar{1}10]}(H=0)=\sqrt{2}M_r/4$, instead of zero, as observed in the previous case, for which both cubic and uniaxial easy axes were along the [110] direction.

In summary, our studies have demonstrated the rich characteristics of magnetic anisotropies in (Ga,Mn)As/GaAs, which – in addition to epitaxial strain – vary with the hole and Mn concentrations as well as with the temperature. According to theory,[7,8] these reflect spin anisotropy of the valence band subbands whose shape depends on strain, while their splitting and population on magnetization and hole concentration. At the same time, our findings have provided the magnetic corroboration for the existence of uniaxial in-plane anisotropy. By group theoretical considerations we have linked this unexpected anisotropy to the top/bottom symmetry breaking, a suggestion calling for a microscopic modelling. Furthermore, in view of our results, a complex temperature dependence of spontaneous magnetization and of related properties, suggesting — for instance — the presence of phases with different Curie temperatures, can actually stem from the temperature-induced switching of the easy axis direction. Since this orientation depends on the hole concentration which, in turn, can be varied by the electric field,[18] it appears possible to switch magnetization direction in a field-effect transistor with the channel of a ferromagnetic semiconductor.

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